

TITLE

Abstract of the Disclosure

- 5 A method for forming a semiconductor device (10) includes providing a substrate (20) having a surface; forming an insulating layer (22) over the surface of the substrate (20); forming a first patterned conductive layer (30) over the insulating layer (22); forming a second patterned conductive layer (32) over the first patterned conductive layer (30); forming a patterned non-insulating layer (34) over the second patterned conductive layer (32); and
- 10 selectively removing portions of the first and second patterned conductive layers (30, 32) to form a notched control electrode for the semiconductor device (10).